



FQD6N60CTM_WS Information



For Reference Only

Part Number FQD6N60CTM_WS

Manufacturer Fairchild/ON Semiconductor

Category Discrete Semiconductor Products
Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V DPAK

Package TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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FQD6N60CTM_WS Specifications

Manufacturer Part NumberFQD6N60CTM_WSManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesQFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C4A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs20nC @ 10VInput Capacitance (Ciss) (Max) @ Vds810pF @ 25VVgs (Max)±30VFET Feature-Power Discipation (Max)-Power Discipation (Max)-
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series QFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C AA (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single TO-252-3, DPak (2 Leads + Tab), SC-63 QFET? HOTOLOGY NOSFET (Metal Oxide) 10V 4 (Tc) 10V 10V 10V 10V 10V 10V 10V 10
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Vgs (Max) ±30V FET Feature -
FET Feature -
Power Dissinction (May)
Power Dissipation (Max) 80W (Tc)
Rds On (Max) @ Id, Vgs 2 Ohm @ 2A, 10V
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$
Mounting Type Surface Mount
Supplier Device Package D-Pak
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63
Report error

FQD6N60CTM_WS Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

FQD6N60CTM_WS Payment Methods



















FQD6N60CTM_WS Shipping Methods













If you have any question about FQD6N60CTM_WS, please do not hesitate to contact us!

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